

Form PTO 1449
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NEW APPLICATION

LIST OF REFERENCES CITED BY APPLICANT

APPLICANT

Takashi IPPOSHI, et al.

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GROUP

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA						
	AB						
	AC						
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	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION	
					YES	NO
JN	AO	9-246505	09/19/97	JAPAN (with English Abstract)	///	X
I	AP	9-223667	08/26/97	JAPAN (with English Abstract)	///	X
	AQ	8-213578	08/20/96	JAPAN (with English Abstract)	///	X
	AR					
	AS					
	AT					
	AU					
	AV					

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

JN	AW	M. BRUEL, et al., "SMART CUT": A PROMISING NEW SOI MATERIAL TECHNOLOGY", Proceedings 1995 IEEE International SOI Conference, October 1995, pgs. 178-179
I	AX	N. SATO, et al., "HIGH-QUALITY EPITAXIAL LAYER TRANSFER (ELTRAN) BY BOND AND ETCH-BACK OF POROUS Si", Proceedings 1995 IEEE International SOI Conference, October 1995, pgs. 176-177
	AY	K. OHMI, et al., "Water Jet Splitting of Thin Porous Si for ELTRAN", Extended Abstracts of the 1999 International Conference on Solid State Devices and Materials, Tokyo, 1999, pgs. 354-355
	AZ	H. SAYAMA, et al., "Effect of <100> Channel Direction for High Performance SCE Immune pMOSFET with Less Than 0.15μm Gate Length", 1999 IEEE, IEDM, pgs. 657-660

Examiner JOSEPH NGUYEN

Date Considered 4/10/02

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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